

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for plasma treatment, comprising the steps of:

(a) arranging a substrate in a chamber, wherein the substrate includes an SiC layer and an SiO<sub>2</sub> layer; and

(b) introducing an etching gas into the chamber and converting the etching gas into plasma to etch selectively the SiC layer against the SiO<sub>2</sub> layer, wherein the etching gas includes CHF<sub>3</sub>, as a main fluorocarbon component thereof, and N<sub>2</sub>,

wherein a ratio of CHF<sub>3</sub> flow rate to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.6, and

wherein the SiC layer is etched at a rate of from 150 nm/min or greater.

Claim 2 (Original): The method of claim 1, wherein the SiO<sub>2</sub> layer is a mask layer on the SiC layer, and wherein the mask layer has an opening pattern.

Claim 3 (Original): The method of claim 1, wherein the SiO<sub>2</sub> layer is a base layer of the SiC layer.

Claims 4-11 (Canceled).

Claim 12 (Previously Presented): The method of claim 18, wherein the substrate includes an organic layer and the SiC layer is etched selectively against the organic layer.

Claim 13 (Original): The method of claim 12, wherein the organic layer is a mask layer of the SiC layer and the mask layer has an opening pattern.

Claim 14 (Original): The method of claim 12, wherein the organic layer is a base layer of the SiC layer.

Claims 15-16 (Canceled).

Claim 17 (Original): The method of claim 12, wherein the organic layer is a dielectric layer with a lower dielectric constant.

Claim 18 (Currently Amended): A method for plasma treatment, comprising the steps of:

(a) arranging a substrate in a chamber, wherein the substrate includes an SiC layer;  
and

(b) introducing an etching gas into the chamber and converting the etching gas into plasma to etch the SiC layer, wherein the etching gas includes CHF<sub>3</sub>, as a main fluorocarbon component thereof, and N<sub>2</sub>, the etching gas being essentially free from any material having O, wherein a ratio of CHF<sub>3</sub> flow rate to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.6, and

wherein the SiC layer is etched at a rate of from 150 nm/min or greater.

Claims 19-24 (Canceled).

Claim 25 (Original): The method of claim 18, wherein the substrate includes a SiO<sub>2</sub> layer and the SiC layer is etched selectively against the SiO<sub>2</sub> layer.

Claims 26-27 (Canceled).

Claim 28 (Original): The method of claim 18, wherein a base layer of the SiC layer is a Cu layer.

Claim 29 (Previously Presented): The method of claim 1, wherein the etching gas consists of CHF<sub>3</sub>, N<sub>2</sub> and an inert gas.

Claim 30 (Canceled).

Claim 31 (Previously Presented): The method of claim 1, wherein the SiC layer is etched at a rate of from 150 to 200 nm/min.

Claims 32-33 (Canceled).

Claim 34 (Previously Presented): The method of claim 18, wherein the SiC layer is etched at a rate of from 150 to 200 nm/min.

Claim 35 (Canceled).